SQS405CENW

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Vishay Siliconix

Automotive P-Channel 12 V (D-S) 175 °C MOSFET



Marking code: Q055

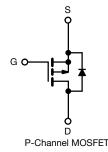
PRODUCT SUMMARY				
V _{DS} (V)	-12			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 V$	0.0220			
I _D (A)	-16			
Configuration	Single			
Package	PowerPAK 1212-8W			

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted	(k	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-12	v
Gate-source voltage ^a		V _{GS}	± 8	v
Continuous drain current ^b	T _C = 25 °C	1-	-16	
	T _C = 125 °C	I _D	-16	
Continuous source current (diode conduction) ^b		I _S	-16	A
Pulsed drain current ^c		I _{DM}	-64	
Single pulse avalanche current L = 0.1 mH		I _{AS}	-16	
Single pulse avalanche energy	L = 0.1 IIIH	E _{AS}	12.8	mJ
Maximum power dissipation	T _C = 25 °C	D	39	w
Maximum power dissipation	T _C = 125 °C	P _D	13	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) e, f			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount d	R _{thJA}	81	°C/W
Junction-to-case (drain)		R _{thJC}	3.8	0/11

Notes

- a. Recommended maximum positive V_{GS} ratings: +4V in continuous mode, +8V in PWM mode with \leq 25% duty
- b. Package limited
- c. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- d. When mounted on 1" square PCB (FR4 material)
- e. See solder profile (www.vishay.com/doc?73257)
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static					I			
Drain-source breakdown voltage	V _{DS}	V _{GS} :	= 0, I _D = -250 μΑ	-12	-	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-0.45	-0.6	-1.0	V	
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -12 V	-	-	-1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -12 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -12 V, T _J = 175 °C	-	-	-150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = -4.5 V$	$V_{DS} \ge -5 V$	20	-	-	А	
		$V_{GS} = -4.5 V$	I _D = -13.5 A	-	0.0106	0.0150		
	P	$V_{GS} = -4.5 V$	I _D = -13.5 A, T _J = 125 °C	-	-	0.0205	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -13.5 A, T _J = 175 °C	I	-	0.0233		
		V _{GS} = -2.5 V	I _D = -12 A	-	0.0166	0.0220	20	
Forward transconductance b	9 _{fs}	V _{DS} = -6 V, I _D = -13.5 A		-	41	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	2260	3050		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -6 V, f = 1 MHz	-	815	1100	pF	
Reverse transfer capacitance	C _{rss}			-	630	850		
Total gate charge ^c	Qg			-	53.6	81		
Gate-source charge ^c	Q _{gs}	$V_{GS} = -8 V$	$V_{DS} = -6 V, I_D = -4 A$	-	4	-	nC	
Gate-drain charge ^c	Q _{gd}	1		-	9.6	-		
Gate resistance	Rg		f = 1 MHz	1.55	3.1	4.65	Ω	
Turn-on delay time ^c	t _{d(on)}			-	11	20		
Rise time ^c	t _r	V _{DD} =	-6 V, R _L = 1.5 Ω	-	6	12	- ns	
Turn-off delay time ^c	t _{d(off)}		$V_{GEN} = -8 V, R_g = 1 \Omega$	-	58	90		
Fall time ^c	t _f			-	26	40		
Source-Drain Diode Ratings and Charact	eristic ^b							
Pulsed current ^a	I _{SM}			-	-	-64	Α	
Forward voltage	V_{SD}	I _F =	-10 A, V _{GS} = 0 V	-	-0.81	-1.1	V	
Body diode reverse recovery time	t _{rr}			-	44	88	ns	
Body diode reverse recovery charge	Q _{rr}		$\Lambda di/dt = 100 \Lambda/iio$	-	32	64	nC	
Reverse recovery fall time	t _a	I _F = -5.	A, di/dt = 100 A/µs	-	22	-		
Reverse recovery rise time	t _b]		-	22	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.2	-	Α	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

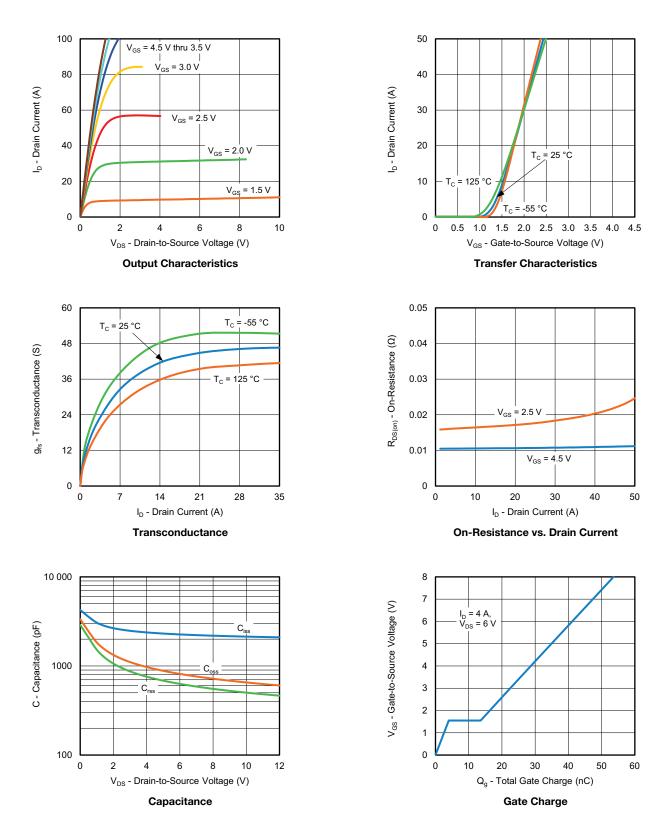
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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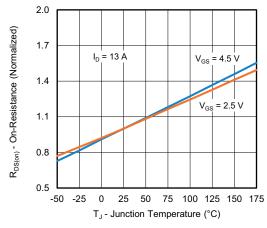
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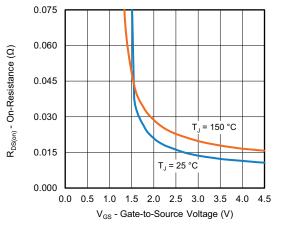
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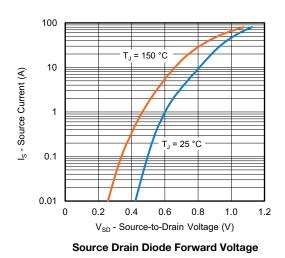
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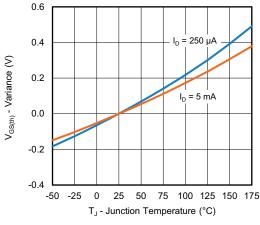


On-Resistance vs. Junction Temperature

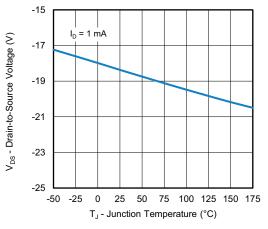


On-Resistance vs. Gate-to-Source Voltage

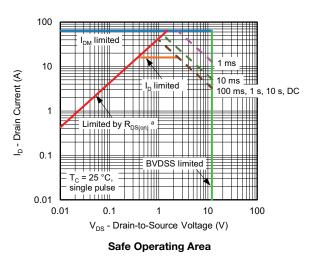




Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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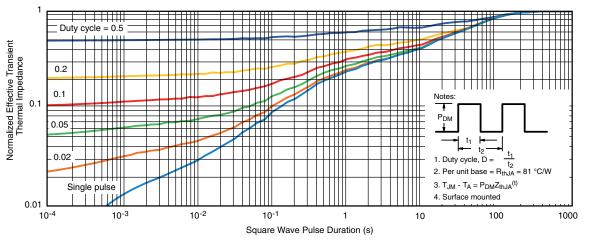
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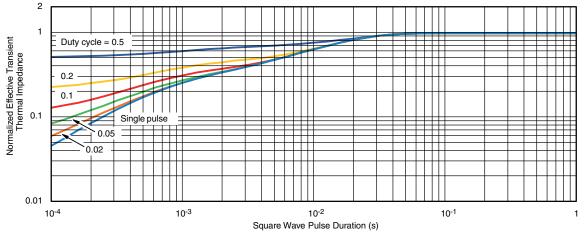




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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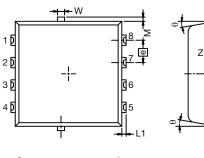
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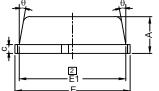


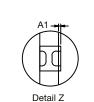
PowerPAK[®] 1212-8W Case Outline

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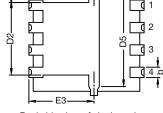




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E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4	0.47 typ.				0.0185 typ.		
D5	2.3 typ.			0.090 typ.			
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.34 typ.			0.013 typ.		
е		0.65 BSC.			0.026 BSC		
К		0.86 typ.		0.034 typ.			
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.				0.005 typ.		
N: C15-1530-R	ev. B, 16-Nov-15						

Backside view of single pad



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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